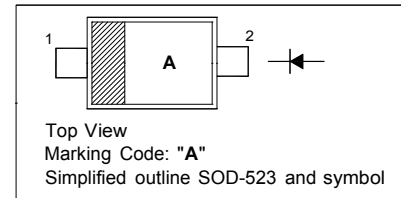


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

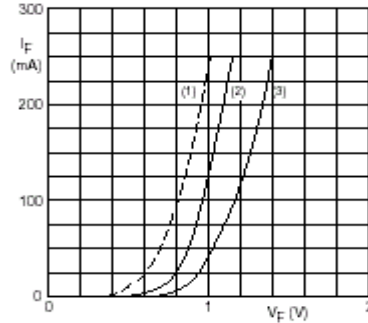


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\ \mu\text{s}$ 4	A
		at $t = 1\ \text{ms}$ 1	
		at $t = 1\ \text{s}$ 0.5	
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

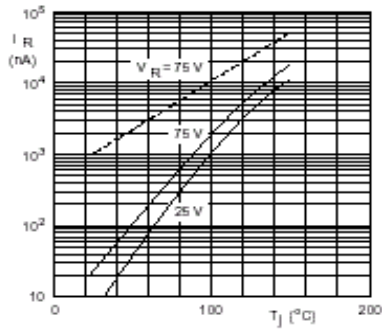
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit				
Forward Voltage at $I_F = 1\ \text{mA}$ at $I_F = 10\ \text{mA}$ at $I_F = 50\ \text{mA}$ at $I_F = 150\ \text{mA}$	V_F	715 855 1000 1250	mV				
Reverse Current at $V_R = 25\ \text{V}$ at $V_R = 75\ \text{V}$ at $V_R = 25\ \text{V}, T_J = 150\text{ }^\circ\text{C}$ at $V_R = 75\ \text{V}, T_J = 150\text{ }^\circ\text{C}$		I_R		30 1 30 50	nA μA μA μA		
Diode Capacitance at $V_R = 0\ \text{V}, f = 1\ \text{MHz}$				C_{tot}		1.5	pF
Reverse Recovery Time at $I_F = 10\ \text{mA}$ to $I_R = 10\ \text{mA}, I_R = 1\ \text{mA}, R_L = 100\ \Omega$				t_{rr}		4	ns



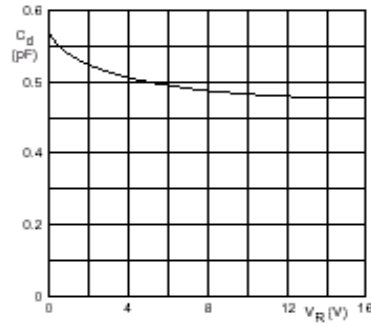
- (1) $T_j = 150\text{ }^\circ\text{C}$; typical values.
- (2) $T_j = 25\text{ }^\circ\text{C}$; typical values.
- (3) $T_j = 25\text{ }^\circ\text{C}$; maximum values.

Forward current as a function of forward voltage.



Dotted line: maximum values.
Solid line: typical values.

Reverse current as a function of junction temperature.



$f = 1\text{ MHz}$; $T_j = 25\text{ }^\circ\text{C}$.

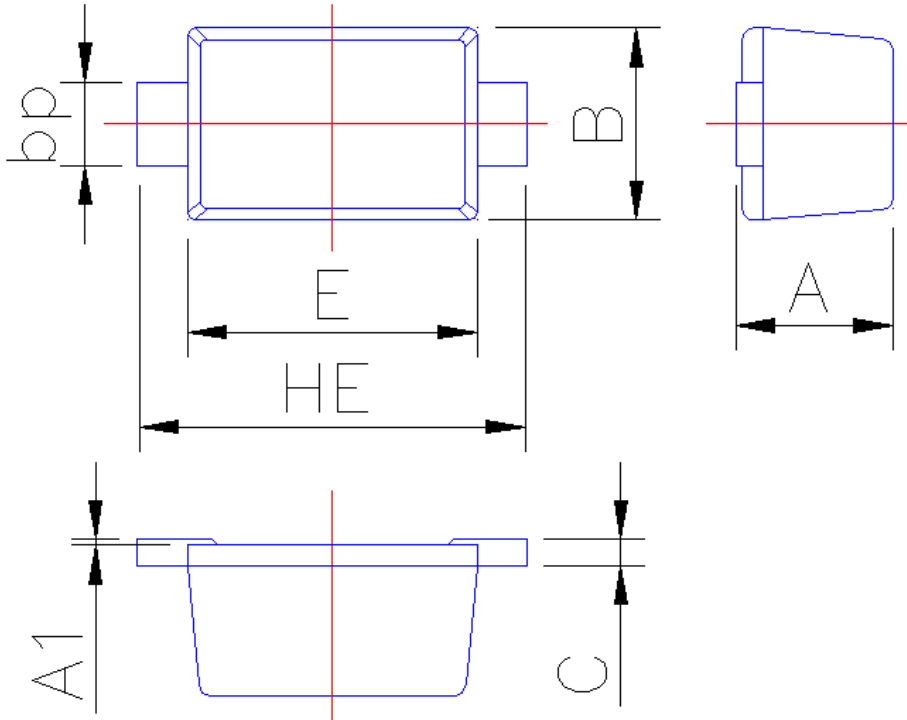
Diode capacitance as a function of reverse voltage; typical values.



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70